SS16

Surface Mount Schottky Power Rectifier

SMA Power Surface Mount Package

These devices employ the Schottky Barrier principle in a large area metal−to−silicon power diode. State of the art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity diodes in surface mount applications where compact size and weight are critical to the system.

Features

- Small Compact Surface Mountable Package with J−Bent Leads
- Rectangular Package for Automated Handling
- Highly Stable Oxide Passivated Junction
- Very Low Forward Voltage Drop
- Guardring for Stress Protection
- Pb−Free Package is Available

Mechanical Characteristics

- Case: Epoxy, Molded, Epoxy Meets UL 94 V−0
- Weight: 70 mg (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Shipped in 12 mm tape, 5000 units per 13 inch reel
- Polarity: Cathode Lead Indicated by Polarity Band
- ESD Ratings: Machine Model = C
  Human Body Model = 3B
- Device Meets MSL 1 Requirements

ON Semiconductor®

http://onsemi.com

SCHOTTKY BARRIER RECTIFIER 1.0 AMPERES 60 VOLTS

SMA
CASE 403D
PLASTIC

MARKING DIAGRAM

SS16 = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

ORDERING INFORMATION

Device	Package	Shipping†
SS16T3	SMA	5000/Tape & Reel
SS16T3G	SMA (Pb−Free)	5000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	60	V
Average Rectified Forward Current (At Rated V_R, T_C = 105°C)	I_O	1.0	A
Non−Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I_{FSM}	40	A
Storage/Operating Case Temperature	T_{stg}, T_C	−55 to +150	°C
Operating Junction Temperature	T_J	−55 to +150	°C
Voltage Rate of Change (Rated V_R, T_J = 25°C)	dv/dt	10,000	V/μs

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction−to−Lead (Note 1) Thermal Resistance, Junction−to−Ambient (Note 1)	$R_{\theta JL}$ $R_{\theta JA}$	35 86	°C/W

ELECTRICAL CHARACTERISTICS

Maximum Instantaneous Forward Voltage (Note 2) (I_F = 0.1 A) (I_F = 1.0 A)	V_F	**T_J = 25°C** 0.51 0.72		V
Maximum Instantaneous Reverse Current (V_R = 60 V)	I_R	**T_J = 25°C** 0.2	**T_J = 100°C** 5.0	mA

1. Mounted on 2 in Square PC Board with 1 in Square Total Pad Size, PC Board FR4.
2. Pulse Test: Pulse Width ≤ 250 μs, Duty Cycle ≤ 2.0%.

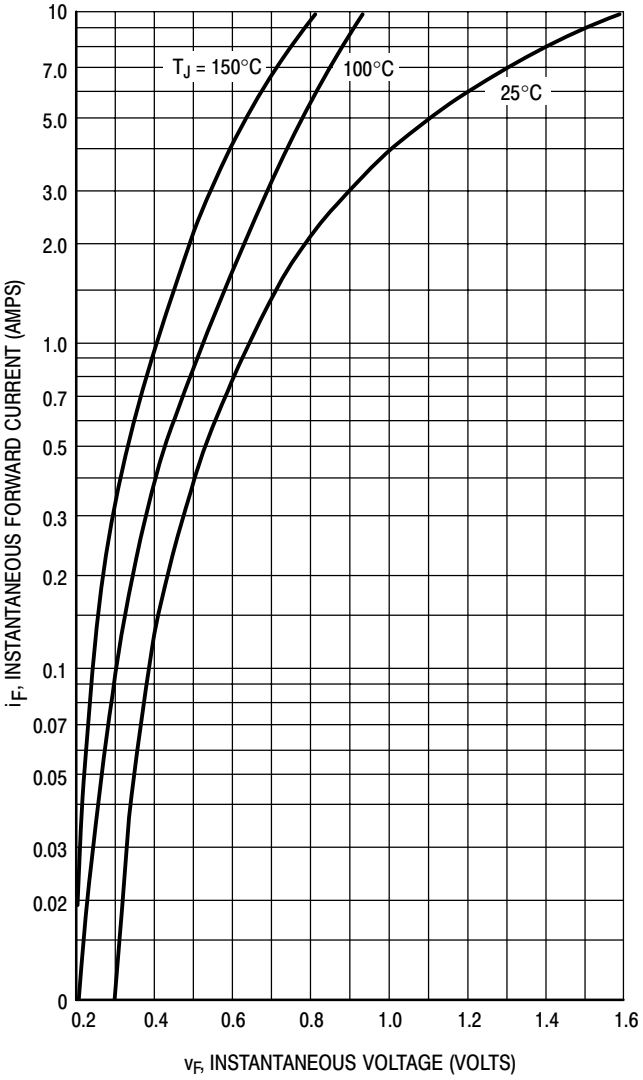


Figure 1. Typical Forward Voltage

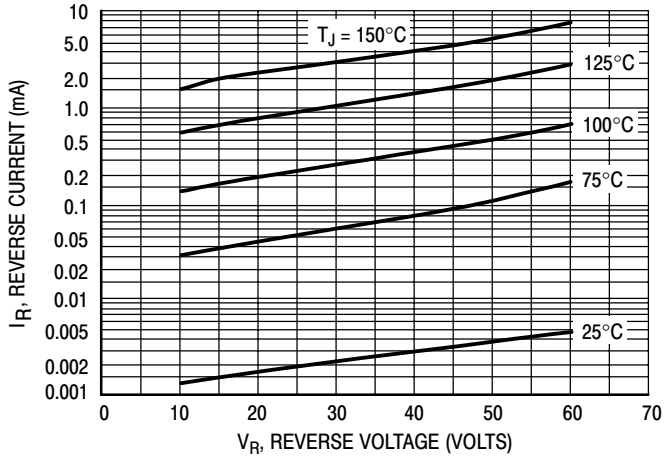


Figure 2. Typical Reverse Current*

*The curves shown are typical for the highest voltage device in the voltage grouping. Typical reverse current for lower voltage selections can be estimated from these same curves if V_R is sufficiently below rated V_R.

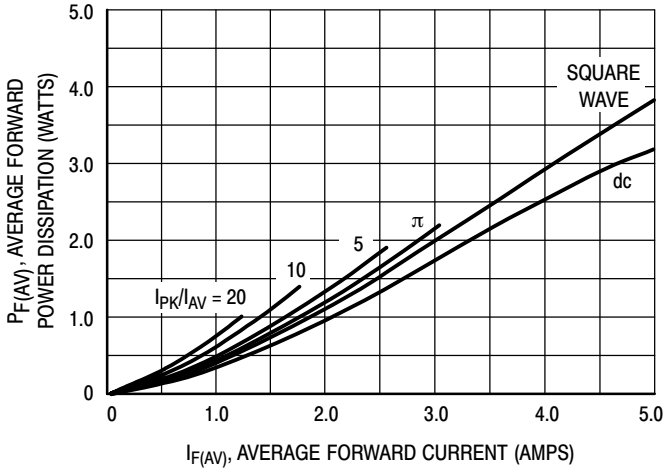


Figure 3. Forward Power Dissipation

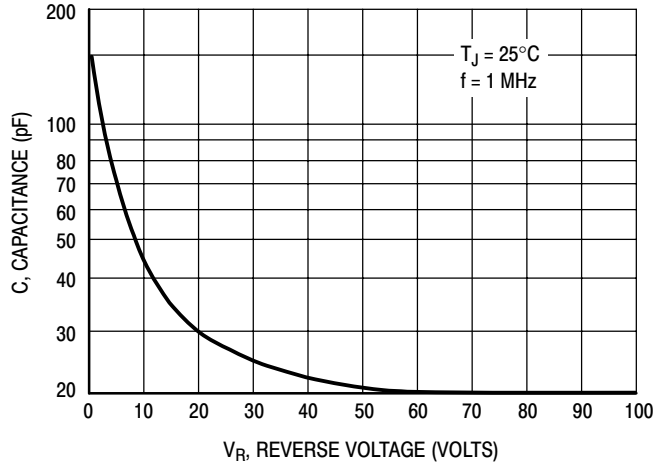
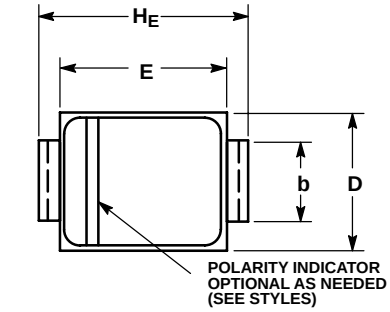


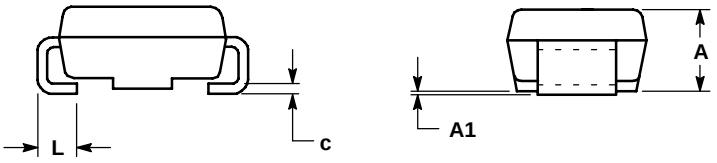
Figure 4. Typical Capacitance

SS16

PACKAGE DIMENSIONS

SMA
CASE 403D−02
ISSUE C



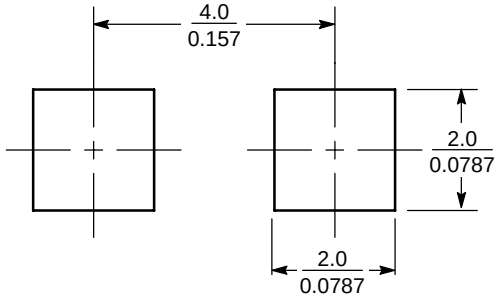


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 403D−01 OBSOLETE, NEW STANDARD IS 403D−02.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	1.91	2.16	2.41	0.075	0.085	0.095
A1	0.05	0.10	0.15	0.002	0.004	0.006
b	1.27	1.45	1.63	0.050	0.057	0.064
c	0.15	0.28	0.41	0.006	0.011	0.016
D	2.29	2.60	2.92	0.090	0.103	0.115
E	4.06	4.32	4.57	0.160	0.170	0.180
H_E	4.83	5.21	5.59	0.190	0.205	0.220
L	0.76	1.14	1.52	0.030	0.045	0.060

STYLE 1:
PIN 1. CATHODE (POLARITY BAND)
2. ANODE

SOLDERING FOOTPRINT*



SCALE 8:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
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